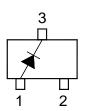
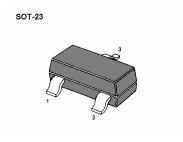
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification and switching power supply power supply applications

Feature

Ultra Low V_F





SOT-23 Plastic Package

Marking

Marking Code: FJ

Absolute Maximum Ratings (T_a= 25°C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	25	V
DC Reverse Voltage	V _R	20	V
DC Forward Current	I _F	1	А
Peak Forward Surge Current 1)	I _{FSM}	3	А
Junction Temperature	Tj	125	°C
Storage Temperature Range	T _s	-40 to +125	°C

 $^{^{1)}}$ 60Hz for 1 \bigcirc

Characteristics at T_a = 25 °C

Parameter	Symbol	Min	Max	Unit
Forward Voltage at I _F = 1 A	V_{F}	-	0.45	V
Reverse Current at V _R = 20 V	I _R	1	200	μΑ

Note: ESD sensitive product handling required.









(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

SEMTECH ELECTRONICS LTD.

● Electrical characteristic curves (Ta=25°C) 10000 G (PE) CURRENT: IR (m.A) € TERMINAL CAPACITANCE FORWARD REVERSE REVERSE VOLTAGE: Vr (V) REVERSE VOLTAGE: VR (V) FORWARD VOLTAGE: VF (V) Fig.3 Capacitance between Fig.1 Forward characteristics Fig.2 Reversecharacteristics terminals characteristics FORWARD POWER DISSIPATION: PF (M) FORWARD CURRENT: RECTIFIED AVERAGE P AMBIENT TEMPERATURE: Ta (°C) AVERAGE RECTIFIED FORWARD CURRENT: Io (A) Fig.5 Derating curve (lo - Ta) Fig.4 Forward power dissipation characteristics











Dated: 13/12/2005